

IN THE CLAIMS:

Please cancel Claims 1-5.

Please add new Claims 6-14:

1-5 (Currently Cancelled)

6. (New) A substrate system comprising a mixture of (i) a refractory metal component selected from the group consisting of tantalum powders, tantalum nitride powders, niobium powders, niobium nitride powders and (ii) a silicon component, wherein (a) the system has a capacitance that is at least 10,000 CV and (b) the silicon is present in an amount that is at least 500 ppm.

7. (New) The substrate system of Claim 6, wherein the silicon is present in an amount ranging from 2 to 10 wt. %.

8. (New) The substrate system of Claim 6, wherein the refractory metal component is present in an amount ranging from 90 to 98 wt.%.

9. (New) The substrate system of Claim 6, wherein the substrate system has capacitance is that is at least 30,000 CV.

10. (New) A substrate system comprising a mixture of (i) a refractory metal component selected from the group consisting of tantalum powders, tantalum nitride powders, niobium powders, niobium nitride powders, the refractory metal component being present in an amount ranging from 90 to 98 wt.% and (ii) a silicon component, wherein (a) the system has a capacitance that is at least 10,000 CV and (b) the silicon is present in an amount ranging from 2 to 10 wt. %.

11. (New) The substrate system of Claim 10, wherein the substrate system has capacitance is that is at least 30,000 CV.

12. (New) A capacitor comprising a substrate system containing a mixture of (i) a refractory metal component selected from the group consisting of tantalum powders, tantalum nitride powders, niobium powders, niobium nitride powders and (ii) a silicon component, wherein (a) the system has a capacitance that is at least 10,000 CV and (b) the silicon is present in an amount that is at least 500 ppm.

13. (New) The substrate system of Claim 6, wherein the silicon is present in an amount ranging from 2 to 10 wt. %.

14. (New) The substrate system of Claim 6, wherein the tantalum or the niobium is present in an amount ranging from 90 to 98 wt.%.